

# PRODUCT INFORMATION LETTER

PIL IPD-DIS/13/8059 Dated 19 Aug 2013

SO8 Super High Density leadframe qualification in ST in-house China plant

Sales Type/product family label	SO8 package
, , ,	1 0
Type of change	Package assembly material change
Reason for change	to optimize the industrial process
Description	Implementation of Super High Density frame with die Attach pad optimization on products housed in SO8 package
Forecasted date of implementation	12-Aug-2013
Forecasted date of samples for customer	12-Aug-2013
Forecasted date for <b>STMicroelectronics</b> change Qualification Plan results availability	12-Aug-2013
Involved ST facilities	ST in-house China plant

#### **DOCUMENT APPROVAL**

Name	Function
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(1) IPG: Industrial & Power Group - ASD: Application Specific Device – IPAD™: Integrated Passive and Active Devices

## PIL Product/Process Information Letter

Notification number:	IPG-DIS/13/8059	Issue Date	12/08/2013	
Issued by	Aline AUGIS		I	
Product series affected	by the change	CLP190ERL		
		CLP30-200B1RL		
		ETP01-1621RL		
		ETP01-2821RL		
		LCDP1521RL		
		LCDP1521SRL		
		LCP1521S		
		LCP1521SRL		
		LCP1531RL		
		PEP01-5841		
		QPS200BRL		
		THBT15011DRL		
		THBT20011D/DRL		
		TPI12011N/NRL		
		TPI8011N/NRL		
		TPN3021/RL		
		1		

#### Reason for change

ST upgrades its products housed in SO8 package with a new Super High Density frame in order to optimize its industrial process.

TPP25011RL

#### Effects of change

Implementation of Super High Density frame with die Attach pad optimization on products housed in SO8 package

- The changed products do not present modified electrical, dimensional or thermal parameters, leaving unchanged the current information published in the product datasheet
- The Moisture Sensitivity Level of the part (according to the IPC/JEDEC JSTD-020D standard) remains unchanged.
- The footprint recommended by ST remains the same.
- There is no change neither in the packing modes nor the standard delivery quantities.

Issue date 12-08-2013 1/2

#### STMicroelectronics IPD - ASD & IPAD™ Division¹ BU Protection



(1) IPG: Industrial & Power Group - ASD: Application Specific Device – IPAD™: Integrated Passive and Active Devices

#### Product identification and traceability

Traceability and identification is ensured by:

- Specific **internal product codification** for devices with Super High Density leadframe. This code is mentioned on the inner and outer packing box.
- QA lot number .

**Qualification complete date** 

8<sup>th</sup> of April, 2013

#### Forecasted sample availability

Product family	Package	Commercial part Number	Availability date
Protection	SO8	LCP1521S	Now
Protection	SO8	TPN3021	Now
Protection	SO8	LCP1531	Now
Protection	SO8	TPI12011NRL	Now
Protection	SO8	TPI8011NRL	Now
Protection	SO8	PEP01-5841	Now

#### Change implementation schedule

Sales types	Estimated production start	Estimated first shipments
All SO8	Week 30-2013	Week 36-2013

Issue date 12-08-2013 2/2



## External Reliability Evaluation Report SO8 Super High Density leadframe qualification in ST China plant

Gen	eral Information			
Product Line	P&L58 anP&L80			
	ACS102-6T1-TR			
	CLP190ERL			
	CLP30-200B1RL			
	ETP01-1621RL			
	ETP01-2821RL			
	LCDP1521RL			
	LCDP1521SRL			
	LCP1521S			
	LCP1521SRL			
P/N	LCP1531RL			
	PEP01-5841			
	QPS200BRL			
	THBT15011DRL			
	THBT/30/11D/DRI			
	TPI12011N/NRL			
	TPI8011N/NRL			
	TPN3021/RL			
	TPP25011RL			
Product Group	IPD			
Product division	ASD & IPAD			
Package	S08			
Maturity level step	30			

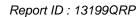
Locations					
Wafer fab	ST Tours (France)				
Assembly plant	ST Shenzhen (China)				
Reliability Lab	STM Tours(France)				
Reliability assessment	Pass				

#### **DOCUMENT INFORMATION**

Version	Date	Pages	Prepared by	Approved by	Comment
1.0	25/07/2013	12	J.Michelon	JP.Rebrasse	Report supporting PIL 7970

Note: This report is a summary of the reliability trials performed in good faith by STMicroelectronics in order to evaluate the potential reliability risks during the product life using a set of defined test methods.

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## 1 APPLICABLE AND REFERENCE DOCUMENTS

Document reference	Short description		
JESD47	Stress-Test-Driven Qualification of Integrated Circuits		
SOP 2614	Reliability requirements for product qualification		
0061692	Reliability tests and criteria for qualifications		

## 2 GLOSSARY

DUT	Device Under Test	
PCB	Printed Circuit Board	
SS	Sample Size	
TC	Temperature Cycling	
THB	Temperature Humidity Bias	
HTOL	High Temperature Operational Life	
DT	Drop Test	





#### **3 RELIABILITY EVALUATION OVERVIEW**

#### 3.1 Objectives

ST upgrades its products housed in SO8 package with a new Super High Density frame in order to optimize its industrial process.

#### 3.2 Conclusion

Qualification Plan requirements have been fulfilled without exception. Reliability tests have shown that the devices behave correctly against environmental tests (no failure). Moreover, the stability of electrical parameters during the accelerated tests demonstrates the robustness of the products and safe operation, which is consequently expected during their lifetime.





## 4 TESTS RESULTS SUMMARY

## 4.1 **Test vehicle**

Lot #	Part Number	Die manufacturing site	Assembly Site	Package	Comments
Lot 1	PEP01-5841	ST Tours (France)	ST Shenzhen (China)	SO8	Qualification Lot
Lot 2	TPN3021RL	ST Tours (France)	ST Shenzhen (China)	SO8	Qualification Lot
Lot 3	LCP1521S	ST Tours (France)	ST Shenzhen (China)	SO8	Qualification Lot
Lot 4	ACS102-6T1-TR	ST Tours (France)	ST Shenzhen (China)	SO8	Qualification Lot
Lot 5	TPP25011RL	ST Tours (France)	ST Shenzhen (China)	SO8	Qualification Lot





## 4.2 **Test plan and results summary**

#### PEP01-5841

Test	РС	Std ref.	Conditions	SS	Steps	Failure/SS Lot 1	Note
Die Oriented Tes	Die Oriented Tests						
					168h	0/77	
HTRB	N	JESD22 A-108	Tj = 150°C; VR = 58V	77	500h	0/77	
					1000h	0/77	
Package Oriente	ed Te	ests					
MSL 1	N	JESD 22 A-113	Ta = 85°C / RH = 85% 3 IR Reflows: Tp = 260°C	25	168h	0/25	MSL1 validated
			Ta = 85°C / RH = 85%	77	168h	0/77	
THB	Υ	JESD22 A-101			500h	0/77	
			VR = 58V		1000h	0/77	
TC	Υ	JESD22 A-104	-65°C / +150°C 2 cycles / hour	77	500C	0/77	
UHAST	Υ	JESD22 A-118	Ta =130°C / RH=85% 3 BARS	77	96h	0/77	
Solderability	N	JESD22 B-102	Steam Ageing 8h SnAgCu 245°C	15	Visual Inspection	0/15	
Solderability	N	JESD22 B-102	Steam Ageing 8h SnPb 220°C	15	Visual Inspection	0/15	
Solderability	N	JESD22 B-102	Dry Ageing 16h SnAgCu 245°C	15	Visual Inspection	0/15	
Solderability	N	JESD22 B-102	Dry Ageing 16h SnPb 220°C	15	Visual Inspection	0/15	





#### TPN3021RL

Test	РС	Std ref.	Conditions	SS	Steps	Failure/SS Lot 2	Note
Die Oriented Te	Die Oriented Tests						
					168h	0/77	
HTS	N	JESD22 A-103	To 450°C	77	500h	0/77	
піз	IN	JESD22 A-103	Ta = 150°C	77	1000h	0/77	
					2000h	0/77	
Package Oriente	Package Oriented Tests						
					168h	0/77	
THB	Υ	JESD22 A-101	Ta = 85°C / RH = 85%	77	500h	0/77	
IUD	r		VR = 28V	11	1000h	0/77	
					2000h	0/77	



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#### LCP1521S

Test	РС	Std ref.	Conditions	SS	Steps	Failure/SS Lot 3	Note
Die Oriented Te	Die Oriented Tests						
					168h	0/77	
HTRB	N	JESD22 A-108	Tj = 150°C / VR = 175V	77	500h	0/77	
					1000h	0/77	
Package Oriento	ed Te	ests					
MSL 1	N	JESD 22 A-113	Ta = 85°C / RH = 85% 3 IR Reflows : Tp = 260°C	25	168h	0/25	MSL1 validated
			T- 050C / DIL 050/		168h	0/77	
THB	Υ	JESD22 A-101	Ta = 85°C / RH = 85% VR = 100V	77	500h	0/77	
			VR = 100V		1000h	0/77	
TC	Υ	JESD22 A-104	-65°C / +150°C 2 cycles / hour	77	500C	0/77	
AC	Υ	JESD22 A-102	Ta = 121°C / RH = 100% 2 BAR	25	96h	0/25	
UHAST	Υ	JESD22 A-118	Ta =130°C / RH=85% 3 BARS	25	96h	0/25	
Solderability	N	JESD22 B-102	Steam Ageing 8h SnAgCu 245°C	15	Visual Inspection	0/15	
Solderability	N	JESD22 B-102	Steam Ageing 8h SnPb 220°C	15	Visual Inspection	0/15	
Solderability	N	JESD22 B-102	Dry Ageing 16h SnAgCu 245°C	15	Visual Inspection	0/15	
Solderability	N	JESD22 B-102	Dry Ageing 16h SnPb 220°C	15	Visual Inspection	0/15	





#### ACS102-6T1-TR

Test	РС	Std ref.	Conditions	ss	Steps	Failure/SS Lot 4	Note
Die Oriented Te	Die Oriented Tests						
					168h	0/77	
HTRB	N	JESD22 A-108	Tj = 125°C / 600VAC Peak	77	500h	0/77	
					1000h	0/77	
Package Oriento	ed Te	ests					
MSL 1	N	JESD 22 A-113	Ta = 85°C / RH = 85% 3 IR Reflows: Tp = 260°C	25	168h	0/25	MSL1 validated
тс	Υ	JESD22 A-104	-65°C / +150°C 2 cycles / hour	77	500C	0/77	
RSH	Υ	JESD22 B-106	260°C; 10s ON; 15s OFF 2 cycles	77	2 Dipping	0/12	
Solderability	N	JESD22 B-102	Steam Ageing 8h SnAgCu 245°C	15	Visual Inspection	0/15	
Solderability	N	JESD22 B-102	Steam Ageing 8h SnPb 220°C	15	Visual Inspection	0/15	
Solderability	N	JESD22 B-102	Dry Ageing 16h SnAgCu 245°C	15	Visual Inspection	0/15	
Solderability	N	JESD22 B-102	Dry Ageing 16h SnPb 220°C	15	Visual Inspection	0/15	

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#### TPP2501RL

Test	РС	Std ref.	Conditions	SS	Steps	Failure/SS Lot 6	Note
Package Oriented Tests							
MSL 1	N	JESD 22 A-113	Ta = 85°C / RH = 85% 3 IR Reflows: Tp = 260°C	30	168h	0/30	
THS	N	JESD22 A-118	Ta = 85°C / RH = 85%	30	1000h	0/30	



## 5 ANNEXES

## **Tests Description**

Test name	Description	Purpose
Die Oriented		
HTRB High Temperature Reverse Bias	The device is stressed in static configuration, trying to satisfy as much as possible the following conditions: low power dissipation; max. supply voltage compatible with diffusion process and internal circuitry limitations;	accelerated way.  To maximize the electrical field across either reverse-biased junctions or dielectric layers, in
Package Oriented		
RSH Resistance to Solder Heat	device is submitted to a dipping in a solder bath at 260°C with a dwell time of 10s. Only for through hole mounted devices.	conducted through the leads into the device package from solder heat at the reverse side of the board. This procedure does not simulate wave soldering or reflow heat exposure on the same side of the board as the package body.
u-HAST unbiased High Accelerated Stress Test	The device is un-biased under 130°C 85% RH during 96 hours	The Highly-Accelerated Temperature and Humidity Stress Test is performed for the purpose of evaluating the reliability of non-hermetic packaged solid-state devices in humid environments. It employs severe conditions of temperature, humidity, and bias which accelerate the penetration of moisture through the external protective material (encapsulant or seal) or along the interface between the external protective material and the metallic conductors which pass through it. The stress usually activates the same failure mechanisms as the "85/85" Steady-State Humidity Life Test (THB).
PC Preconditioning	temperature profile used for surface	As stand-alone test: to investigate the moisture sensitivity level. As preconditioning before other reliability tests: to verify that the surface mounting stress does not impact on the subsequent reliability performance. The typical failure modes are "pop corn" effect and delamination.
THB Temperature Humidity Bias	The device is biased in static configuration minimizing its internal power dissipation, and stored at controlled conditions of ambient temperature and relative humidity.	To evaluate the package moisture resistance with electrical field applied, both electrolytic and galvanic corrosion are put in evidence.

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Test name	Description	Purpose
<b>TC</b> Temperature Cycling	The device is submitted to cycled temperature excursions, between a hot and a cold chamber in air atmosphere.	Linteracting in the die-nackage system. Lynical i

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